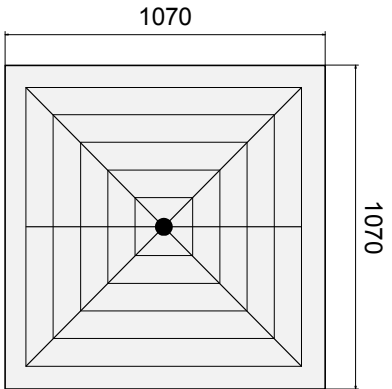


Radiation	Type	Technology	Electrodes
Red	MQW	AlInGaP/Si	N (cathode) up

	typ. dimensions in $\mu\text{m}$ ( $\pm 25 \mu\text{m}$ )
	<u>typ. thickness</u> 225 ( $\pm 25$ ) $\mu\text{m}$  <u>cathode</u> gold alloy, 1.0 $\mu\text{m}$  <u>anode</u> gold alloy, 1.5 $\mu\text{m}$

### Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	$V_F$		1.8	2.3	V
Forward voltage <sup>2</sup>	$I_F = 350 \text{ mA}$	$V_F$		2.4		V
Reverse voltage	$I_R = 10 \mu\text{A}$	$V_R$	10			V
Radiant power <sup>1</sup>	$I_F = 20 \text{ mA}$	$\Phi_e$	4.1	5.4		mW
Radiant power <sup>2</sup>	$I_F = 350 \text{ mA}$	$\Phi_e$		100		mW
Luminous intensity <sup>1</sup>	$I_F = 20 \text{ mA}$	$I_V$	270	350		mcd
Luminous intensity <sup>2</sup>	$I_F = 350 \text{ mA}$	$I_V$		6500		mcd
Peak wavelength <sup>1</sup>	$I_F = 20 \text{ mA}$	$\lambda_P$	620	630	640	nm
Dominant wavelength <sup>2</sup>	$I_F = 350 \text{ mA}$	$\lambda_D$		622		nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		18		nm
Switching time	$I_F = 20 \text{ mA}$	$t_r, t_f$		70/35		ns

<sup>1</sup>Measured on bare chip on TO-18 header

<sup>2</sup>Measured on bare chip on Cu-carrier, 10s current flow (information only)

### Labeling

Type	Lot N°	$I_V(\text{typ})$ [mcd]	$V_F(\text{typ})$ [V]	Quantity
ELC-630-21				

**Packing:** Chips on adhesive film with wire-bond side on top

Note: All measurements carried out with *EPIGAP* equipment